

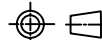

Note:

1. SUBSTRATE:IR MONO GRADE SI
2. GROWING METHOD:CZ
3. CLEAR APERTURE:95%
4. SURFACE QUALITY:S1&S2 60-40 SCRATCH-DIG
5. PARALLELISM:3ARCMIN
6. POWER:5  $\lambda/2$
7. IRREGULARITY:3  $\lambda/2$
8. COATING: NONE

9 FINE GRIND SURFACE

SPECIFICATIONS SUBJECT TO CHANGE  
WITHOUT NOTICE

FOR INFORMATION ONLY  
NOT FOR MANUFACTURE

DRAWING PROJECTION 		ALL DIMS IN	MM
DESIGNED	CHECKED	APPROVED	SCALE
			1:1
MATERIAL	Silicon	TITLE	SI IR-MONO ROUND WINDOW $\phi 25 * T2$
 本征晶体 INTRINSIC CRYSTAL	www.icc-mall.com	DWG NO	PSI01E018
		EDITION	1ST SHEET 1/1